



PSMN4R1-30YLC

N-channel 30 V 4.35mΩ logic level MOSFET in LPAK using NextPower technology

12 February 2013

Product data sheet

1. General description

Logic level enhancement mode N-channel MOSFET in LPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

3. Applications

- DC-to-DC converters
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; Fig. 1	-	-	92	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2	-	-	67	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 20 A; T _j = 25 °C; Fig. 12	-	4.75	5.7	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 12	-	3.65	4.35	mΩ
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 20 A; V _{DS} = 15 V; Fig. 14 ; Fig. 15	-	3.5	-	nC

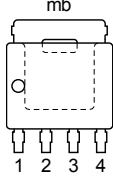
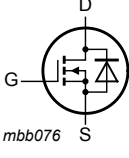


N-channel 30 V 4.35mΩ logic level MOSFET in LPAK using NextPower technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}; I_D = 20\text{ A}; V_{DS} = 15\text{ V};$ Fig. 14 ; Fig. 15	-	11	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK; Power-SO8 (SOT669)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R1-30YLC	LPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R1-30YLC	4C130L

8. Limiting values

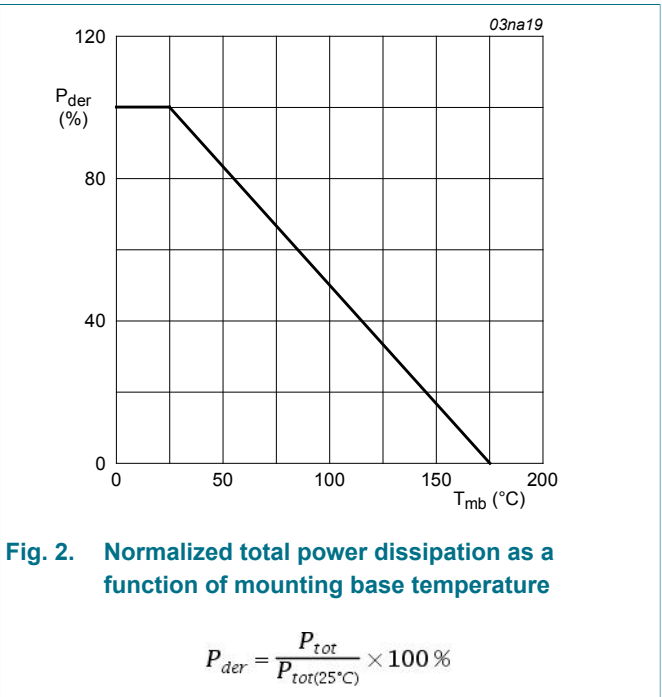
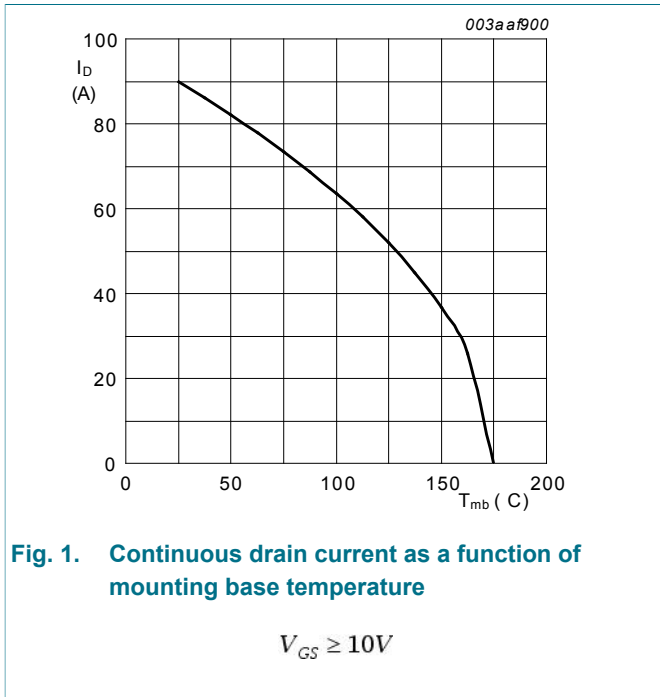
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ Fig. 1	-	92	A
		$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C};$ Fig. 1	-	65	A

N-channel 30 V 4.35mΩ logic level MOSFET in LPAK using NextPower technology

Symbol	Parameter	Conditions	Min	Max	Unit
I_{DM}	peak drain current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 4	-	367	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 2	-	67	W
T_{stg}	storage temperature		-55	175	$^\circ\text{C}$
T_j	junction temperature		-55	175	$^\circ\text{C}$
$T_{sld(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	270	-	V
Source-drain diode					
I_S	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	61	A
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	367	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}$; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$; $I_D = 92 \text{ A}$; $V_{sup} \leq 30 \text{ V}$; $R_{GS} = 50 \text{ } \Omega$; unclamped; Fig. 3	-	21	mJ



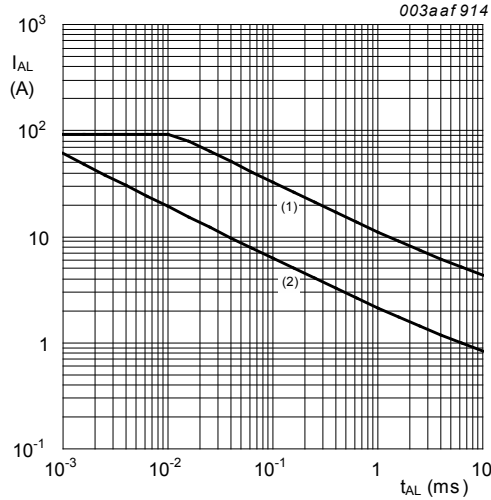


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

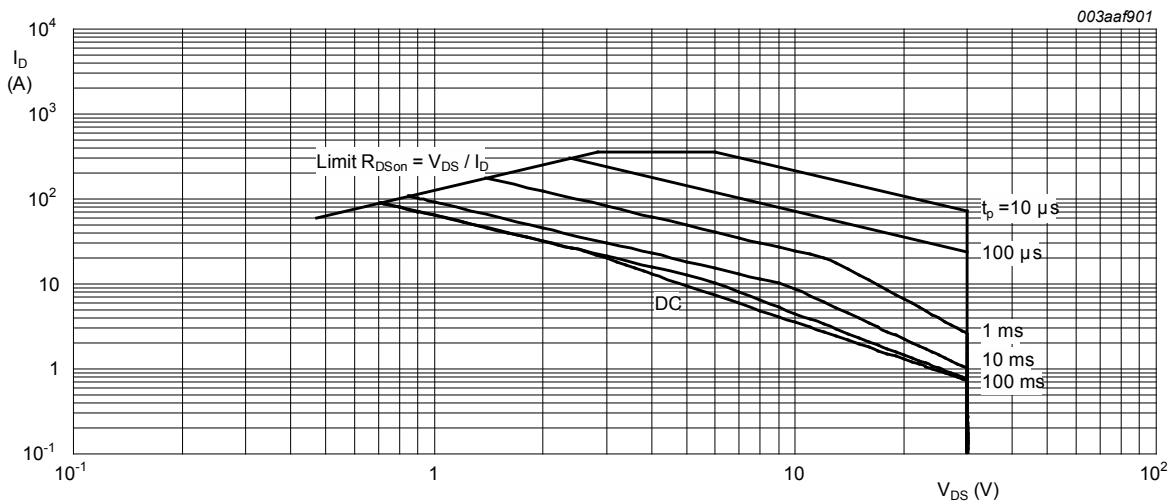


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	2.05	2.24	K/W

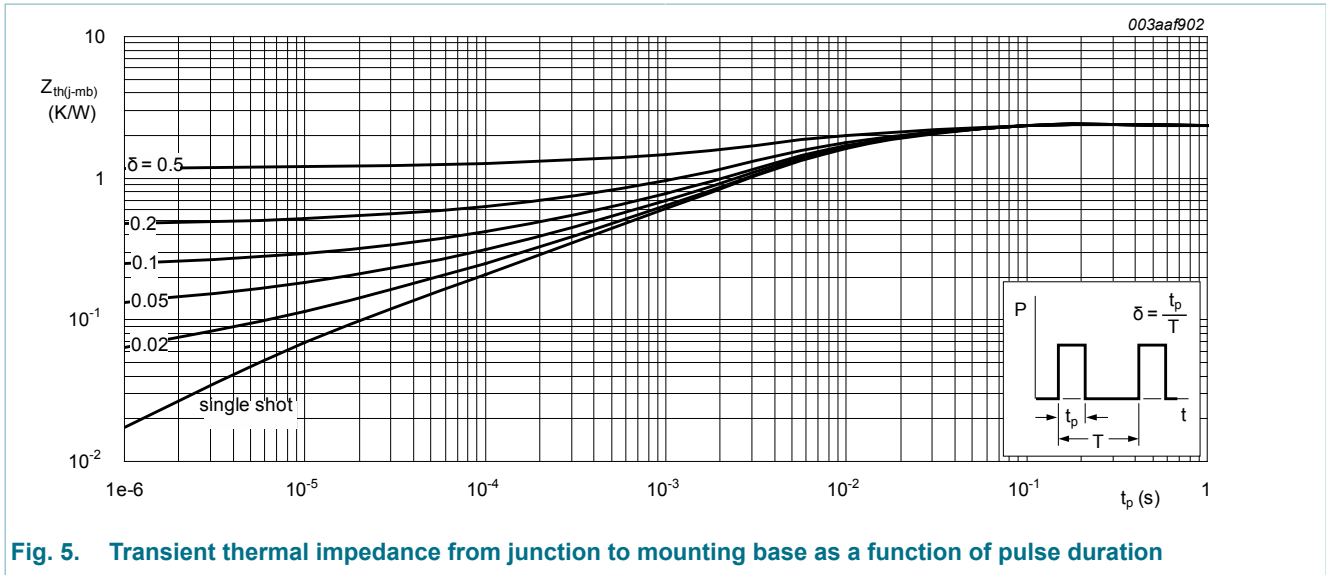


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ Fig. 10 ; Fig. 11	1.05	1.58	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ C$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$	-	-	2.25	V
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ }^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 12	-	4.75	5.7	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ }^\circ C;$ Fig. 12 ; Fig. 13	-	-	9.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 12	-	3.65	4.35	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ }^\circ C;$ Fig. 12 ; Fig. 13	-	-	7.25	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	-	1.9	3.8	Ω

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 14 ; Fig. 15	-	23	-	nC
		I _D = 20 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14 ; Fig. 15	-	11	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	20	-	nC
Q _{GS}	gate-source charge	I _D = 20 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 14 ; Fig. 15	-	3.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	2.3	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1.2	-	nC
Q _{GD}	gate-drain charge		-	3.5	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 20 A; V _{DS} = 15 V; Fig. 14 ; Fig. 15	-	2.66	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 16	-	1502	-	pF
C _{oss}	output capacitance		-	316	-	pF
C _{rss}	reverse transfer capacitance		-	106	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; R _L = 0.6 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 4.7 Ω	-	16	-	ns
t _r	rise time		-	19	-	ns
t _{d(off)}	turn-off delay time		-	24	-	ns
t _f	fall time		-	10	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	8	-	nC
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 20 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 17	-	0.8	1.1	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 15 V	-	23	-	ns
Q _r	recovered charge		-	15	-	nC
t _a	reverse recovery rise time	V _{GS} = 0 V; I _S = 20 A; dI _S /dt = -100 A/μs; V _{DS} = 15 V; Fig. 18	-	13.5	-	ns
t _b	reverse recovery fall time		-	9.5	-	ns

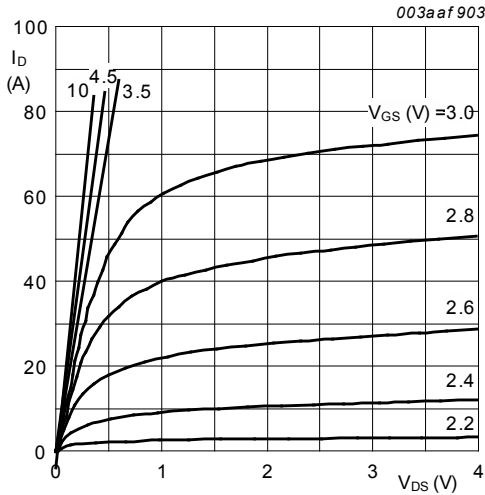


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

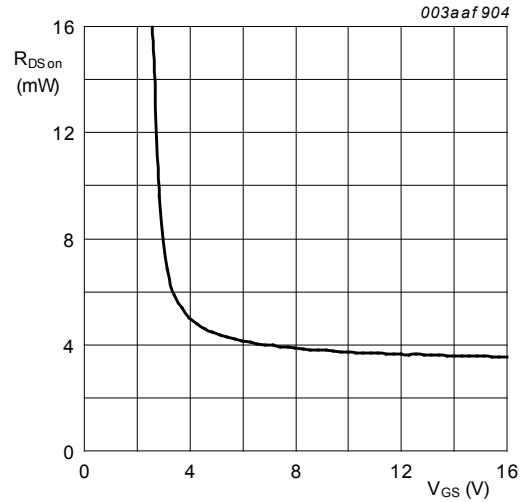


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}; I_D = 20\text{A}$

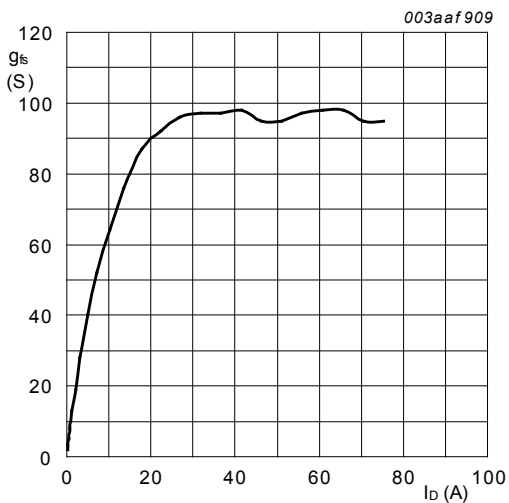


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

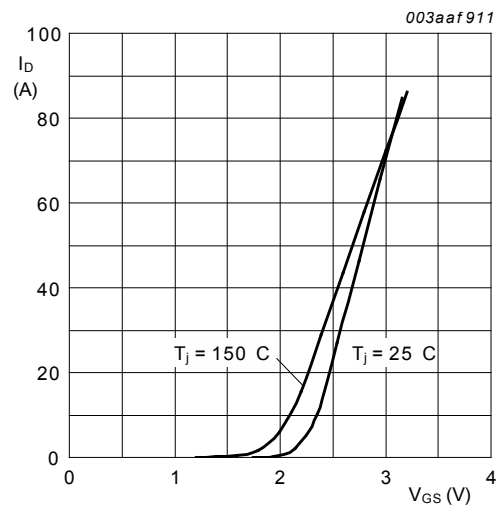


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

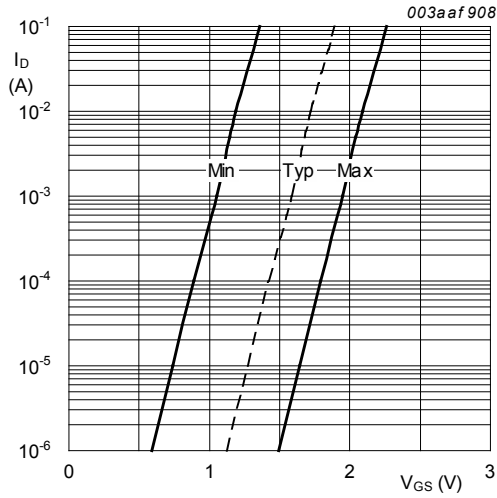


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

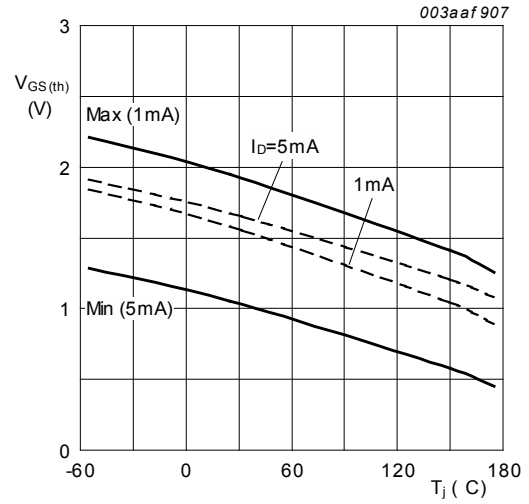


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$V_{DS} = V_{GS}$$

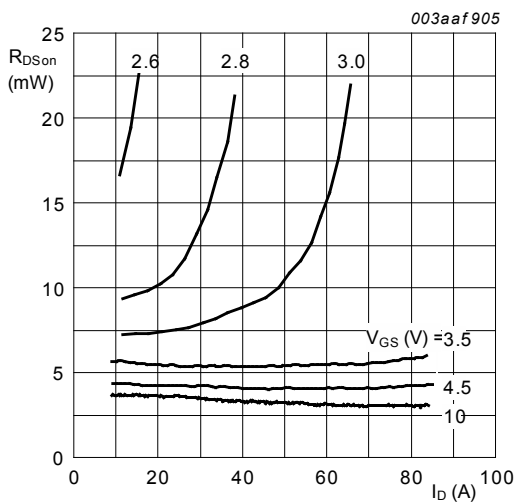


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ\text{C}$$

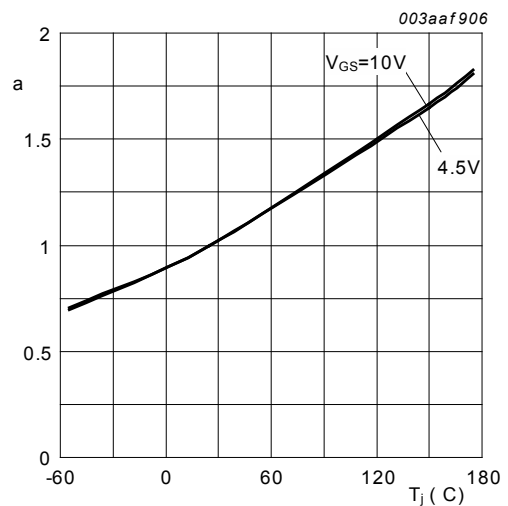


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

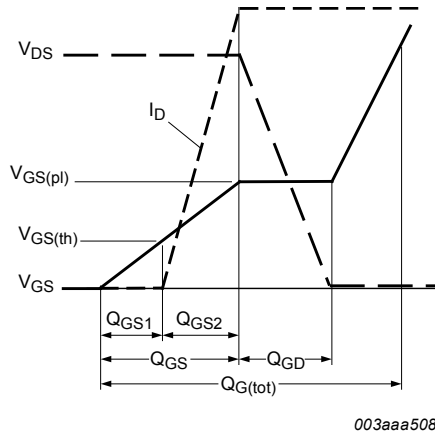


Fig. 14. Gate charge waveform definitions

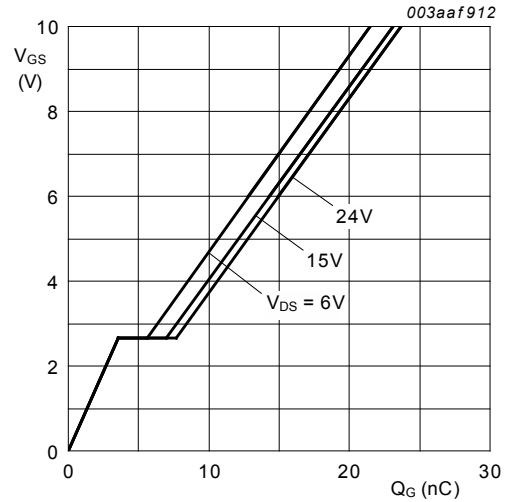


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ C; I_D = 20A$

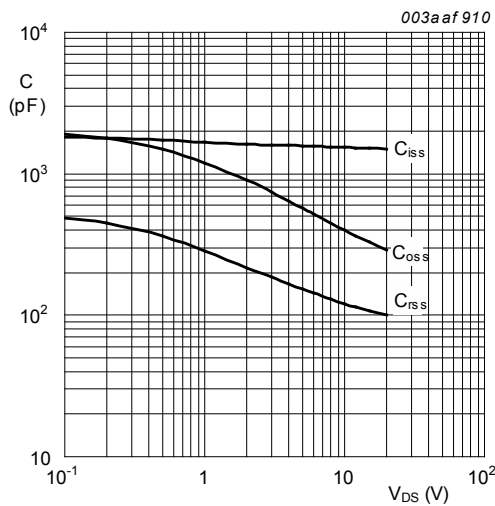


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

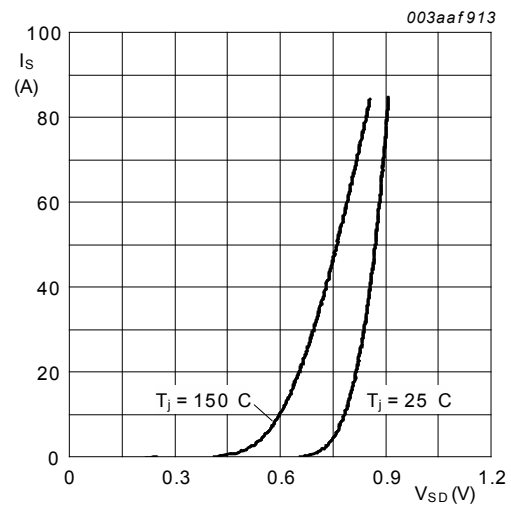


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0V$

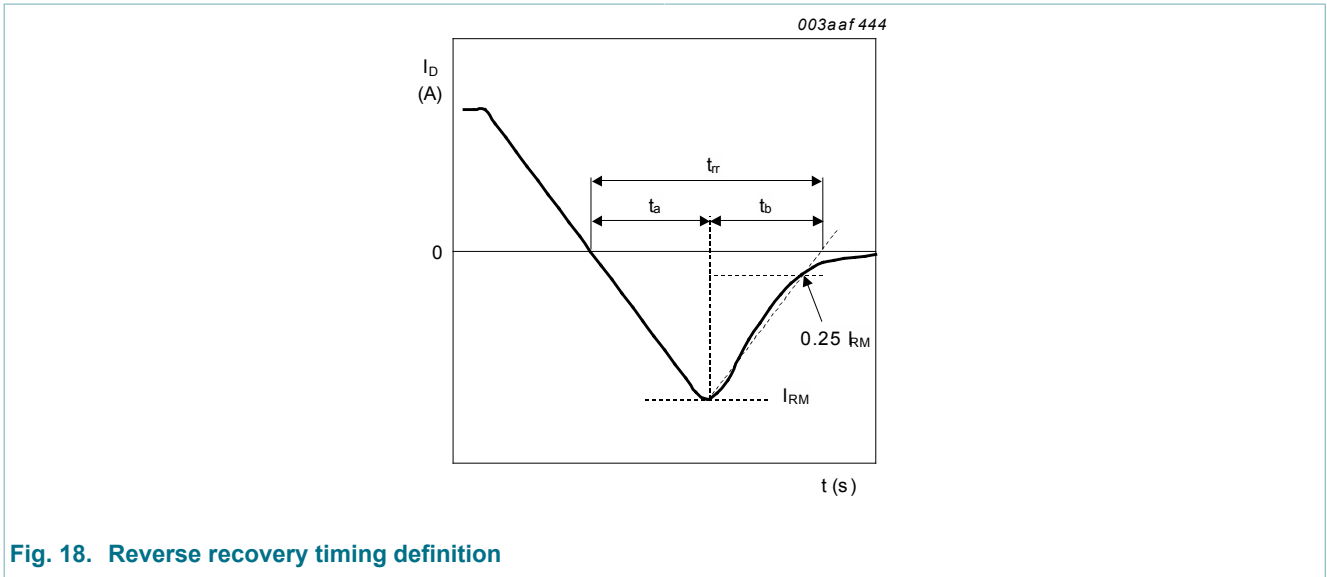
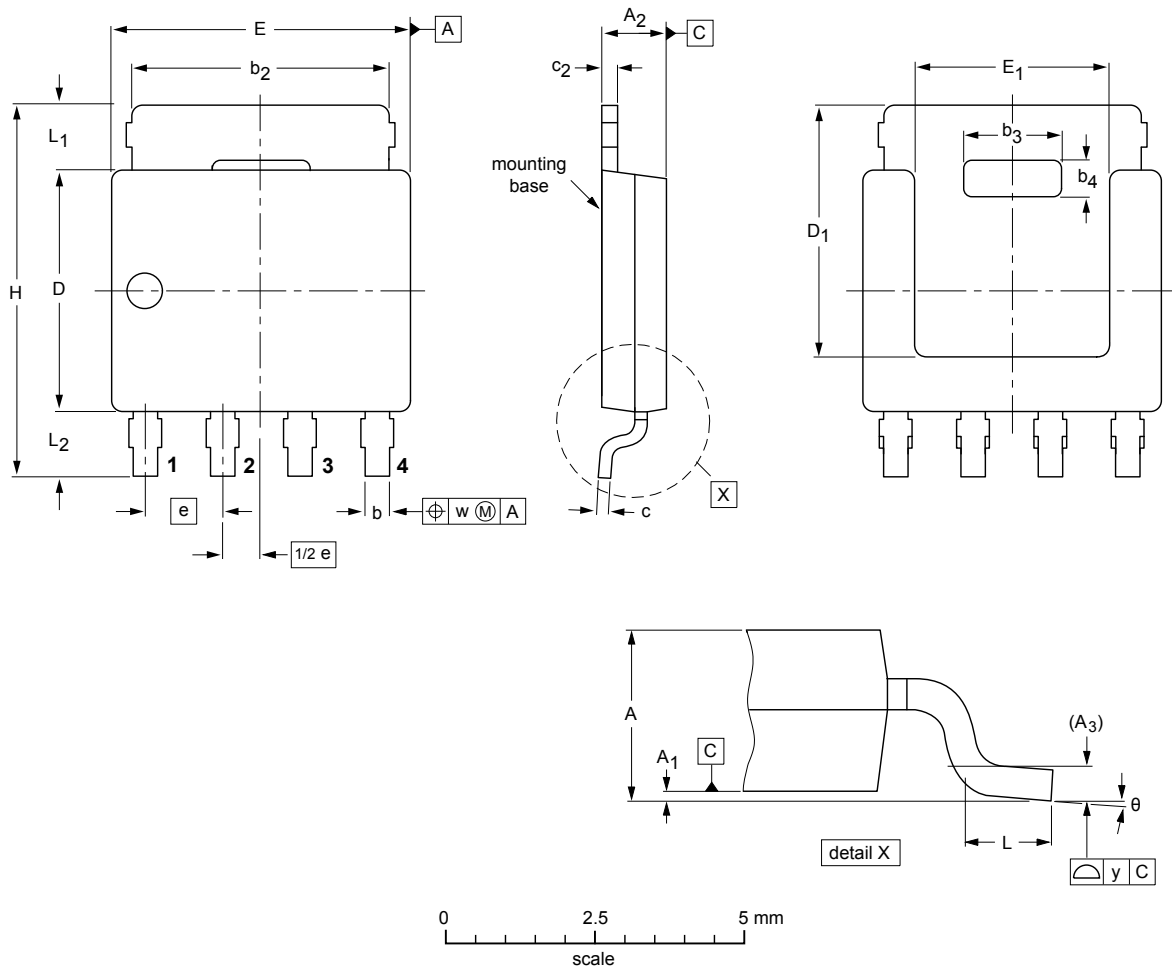


Fig. 18. Reverse recovery timing definition

11. Package outline

Plastic single-ended surface-mounted package (LPAK; Power-SO8); 4 leads

SOT669



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	c	c ₂	D ⁽¹⁾	D ₁ ⁽¹⁾ _{max}	E ⁽¹⁾	E ₁ ⁽¹⁾	e	H	L	L ₁	L ₂	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT669		MO-235				06-03-16 11-03-25

Fig. 19. Package outline LPAK; Power-SO8 (SOT669)

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	11
12	Legal information	12
12.1	Data sheet status	12
12.2	Definitions	12
12.3	Disclaimers	12
12.4	Trademarks	13

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